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IN/Blanchard-Richard-A\$: 65 applications.

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IN/Blanchard-Richard-A\$

PUB. APP. NO.	Title
1 <a href="#">20070117360</a>	<a href="#">Isolated vertical power device structure with both N-doped and P-doped trenches</a>
2 <a href="#">20070035906</a>	<a href="#">Transient blocking unit</a>
3 <a href="#">20070012999</a>	<a href="#">Method for Making a Semiconductor Device Including Regions of Band-Engineered Semiconductor Superlattice to Reduce Device-On Resistance</a>
4 <a href="#">20070012983</a>	<a href="#">Terminations for semiconductor devices with floating vertical series capacitive structures</a>
5 <a href="#">20070012911</a>	<a href="#">Semiconductor Device Including Regions of Band-Engineered Semiconductor Superlattice to Reduce Device-On Resistance</a>
6 <a href="#">20060292889</a>	<a href="#">FINFET Including a Superlattice</a>
7 <a href="#">20060292765</a>	<a href="#">Method for Making a FINFET Including a Superlattice</a>
8 <a href="#">20060267083</a>	<a href="#">Power semiconductor device having a voltage sustaining region that includes doped columns formed with a single ion implantation step</a>
9 <a href="#">20060261407</a>	<a href="#">High-voltage transistor fabrication with trench etching technique</a>
10 <a href="#">20060249788</a>	<a href="#">High voltage power MOSFET having low on-resistance</a>
11 <a href="#">20060238936</a>	<a href="#">Apparatus and method for transient blocking employing relays</a>
12 <a href="#">20060231857</a>	<a href="#">METHOD FOR MAKING A SEMICONDUCTOR DEVICE INCLUDING A MEMORY CELL WITH A NEGATIVE DIFFERENTIAL RESISTANCE (NDR) DEVICE</a>
13 <a href="#">20060226502</a>	<a href="#">Microelectromechanical Systems (MEMS) Device Including a Superlattice</a>
14 <a href="#">20060223215</a>	<a href="#">Method for Making a Microelectromechanical Systems (MEMS) Device Including a Superlattice</a>
15 <a href="#">20060202189</a>	<a href="#">SEMICONDUCTOR DEVICE INCLUDING A MEMORY CELL WITH A NEGATIVE DIFFERENTIAL RESISTANCE (NDR) DEVICE</a>

- 16 20060163690 Semiconductor having thick dielectric regions
- 17 20060134867 Technique for forming the deep doped columns in superjunction
- 18 20060131605 Low capacitance two-terminal barrier controlled TVS diodes
- 19 20060125003 High voltage power MOSFET having low on-resistance
- 20 20060008937 Technique for fabricating multilayer color sensing photodetectors
- 21 20050189586 DMOS device with a programmable threshold voltage
- 22 20050139914 Method for forming thick dielectric regions using etched trenches
- 23 20050110110 Integrated released beam layer structure fabricated in trenches and manufacturing method thereof
- 24 20050095789 Trench DMOS transistor structure having a low resistance path to a drain contact located on an upper surface
- 25 20050054136 Fabrication of diaphragms and "floating" regions of single crystal semiconductor for MEMS devices
- 26 20050042830 High voltage power MOSFET having a voltage sustaining region that includes Doped Columns Formed by trench etching and diffusion from regions of oppositely doped polysilicon
- 27 20050001272 MOSFET device having geometry that permits frequent body contact
- 28 20040251917 Capacitive sensor device with electrically configurable pixels
- 29 20040235250 Symmetric trench MOSFET device and method of making same
- 30 20040178444 Double diffused field effect transistor having reduced on-resistance
- 31 20040175855 TECHNIQUE FOR FABRICATING MEMS DEVICES HAVING DIAPHRAGMS OF "FLOATING" REGIONS OF SINGLE CRYSTAL MATERIAL
- 32 20040164348 High voltage power mosfet having a voltage sustaining region that includes doped columns formed by trench etching using an etchant gas that is also a doping source
- 33 20040157384 Power semiconductor device having a voltage sustaining region that includes doped columns formed with a single ion implantation step
- 34 20040124960 Integrated circuit inductors using driven shields
- 35 20040110333 High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching and ion implantation
- 36 20040097028 Method for fabricating a power semiconductor device having a voltage sustaining layer with a terraced trench facilitating formation of floating islands
- 37 20040070044 High voltage power MOSFET having low on-resistance
- 38 20040036138 High voltage power MOSFET having low on-resistance
- 39 20040032762 DMOS device with a programmable threshold voltage
- 40 20040031989 TWO TERMINAL PROGRAMMABLE MOS-GATED CURRENT SOURCE
- 41 20040009643 METHOD FOR FABRICATING A HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED BY RAPID DIFFUSION
- 42 20030211671 SURFACE GEOMETRY FOR A MOS-GATED DEVICE THAT ALLOWS THE MANUFACTURE OF DICE HAVING DIFFERENT SIZES
- 43 20030209766 Method for using a surface geometry for a MOS-gated device in the manufacture of dice having different sizes
- 44 20030209759 MOSFET DEVICE HAVING GEOMETRY THAT PERMITS FREQUENT BODY CONTACT

- 45 [20030203552](#) [High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching and diffusion from regions of oppositely doped polysilicon](#)
- 46 [20030181010](#) [POWER SEMICONDUCTOR DEVICE HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED WITH A SINGLE ION IMPLANTATION STEP](#)
- 47 [20030173581](#) [Photodiode stacks for photovoltaic relays and the method of manufacturing the same](#)
- 48 [20030122189](#) [High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching using an etchant gas that is also a doping source](#)
- 49 [20030122188](#) [High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching and ion implantation](#)
- 50 [20030075729](#) [Minimum sized cellular MOS-gated device geometry](#)
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51 <a href="#">20030068863</a>	<a href="#">Method for fabricating a power semiconductor device having a floating island voltage sustaining layer</a>
52 <a href="#">20030068854</a>	<a href="#">Method for fabricating a power semiconductor device having a voltage sustaining layer with a terraced trench facilitating formation of floating Islands</a>
53 <a href="#">20030040144</a>	<a href="#">Trench DMOS transistor with embedded trench schottky rectifier</a>
54 <a href="#">20020195655</a>	<a href="#">Symmetric trench MOSFET device and method of making same</a>
55 <a href="#">20020140028</a>	<a href="#">Double diffused field effect transistor having reduced on-resistance</a>
56 <a href="#">20020140025</a>	<a href="#">High voltage power MOSFET having low on-resistance</a>
57 <a href="#">20020132432</a>	<a href="#">Field effect transistor having dielectrically isolated sources and drains and method for making same</a>
58 <a href="#">20020125527</a>	<a href="#">Trench DMOS transistor structure having a low resistance path to a drain contact located on an upper surface</a>
59 <a href="#">20020066924</a>	<a href="#">High voltage power MOSFET having low on-resistance</a>
60 <a href="#">20020017684</a>	<a href="#">Transistor with integrated photodetector for conductivity modulation</a>
61 <a href="#">20020014658</a>	<a href="#">High voltage power mosfet having low on-resistance</a>
62 <a href="#">20020009832</a>	<a href="#">Method of fabricating high voltage power mosfet having low on-resistance</a>
63 <a href="#">20010028578</a>	<a href="#">Method and apparatus for providing an embedded flash-EEPROM technology</a>
64 <a href="#">20010028085</a>	<a href="#">Trench DMOS transistor structure having a low resistance path to a drain contact located on an upper surface</a>
65 <a href="#">20010000111</a>	<a href="#">Field effect transistor having dielectrically isolated sources and drains and method for making same</a>

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